

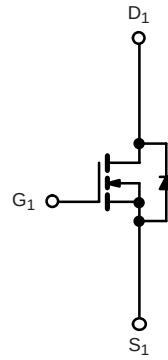
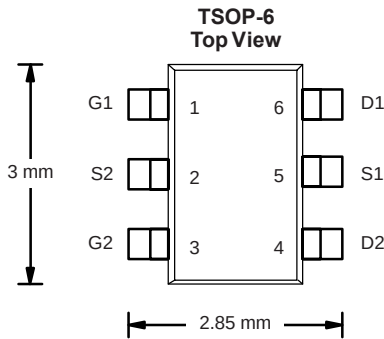
N- and P-Channel 60V (D-S) MOSFET

PRODUCT SUMMARY

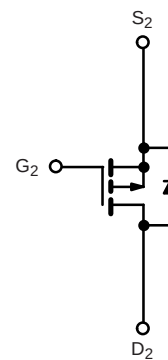
	V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)
N-Channel	60	0.700 at V _{GS} = 10 V	0.80
		0.850 at V _{GS} = 4.5 V	0.75
P-Channel	- 60	2.060 at V _{GS} = - 10 V	- 0.55
		2.410 at V _{GS} = - 4.5 V	- 0.50

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC


RoHS
 COMPLIANT


N-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted

Parameter		Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage		V _{DS}	60	- 60	V
Gate-Source Voltage		V _{GS}	± 20	± 20	
Continuous Drain Current (T _J = 150 °C) ^{a, b}	T _A = 25 °C	I _D	0.8	- 0.55	A
	T _A = 70 °C		0.7	- 0.50	
Pulsed Drain Current		I _{DM}	3.2	-2.2	
Continuous Source Current (Diode Conduction) ^{a, b}		I _S	0.45	- 0.35	
Maximum Power Dissipation ^{a, b}	T _A = 25 °C	P _D	0.75		W
	T _A = 70 °C		0.43		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	R _{thJA}	93	110	°C/W
		130	150	
Maximum Junction-to-Lead	R _{thJL}	75	90	

Notes:

a. Surface Mounted on FR4 board.

b. t ≤ 5 s.

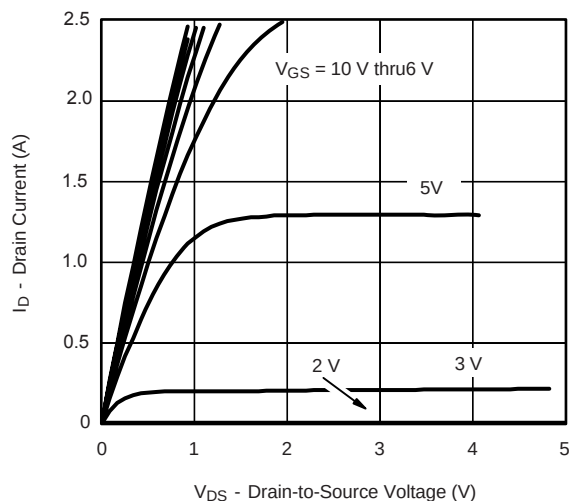
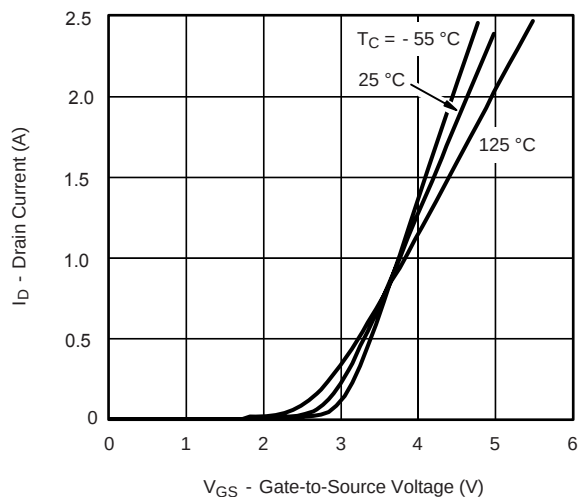
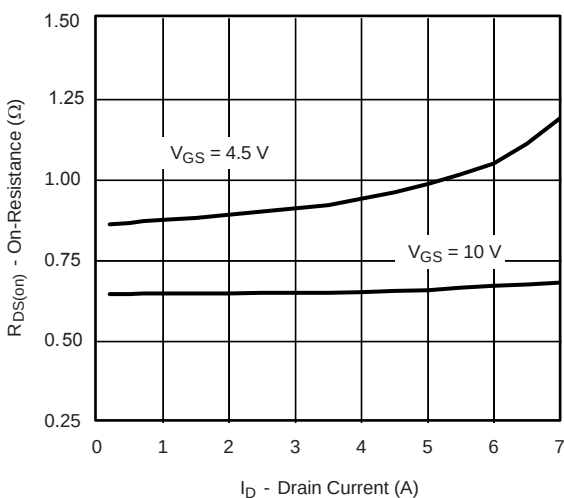
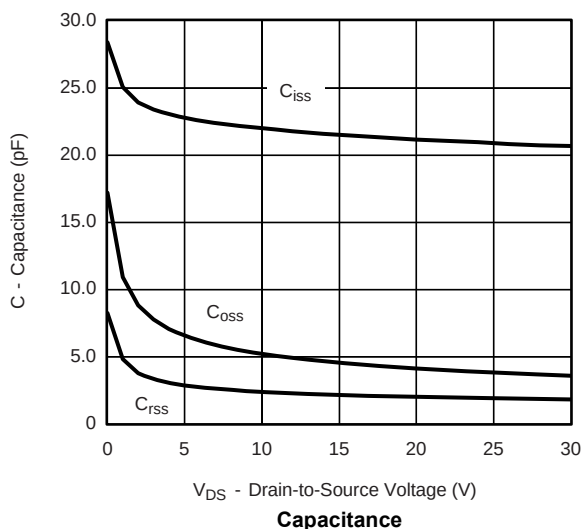
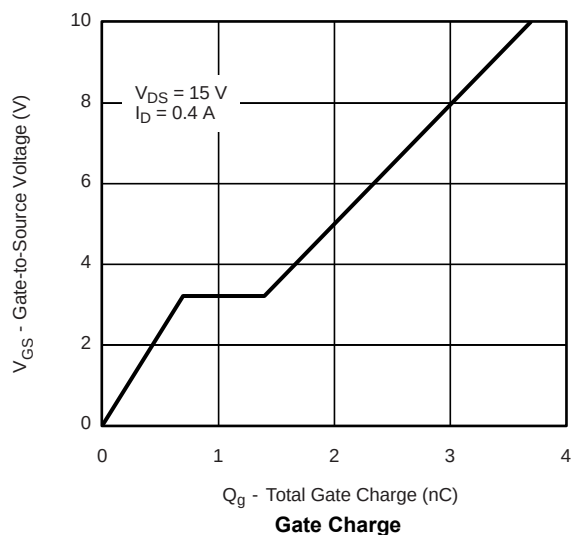
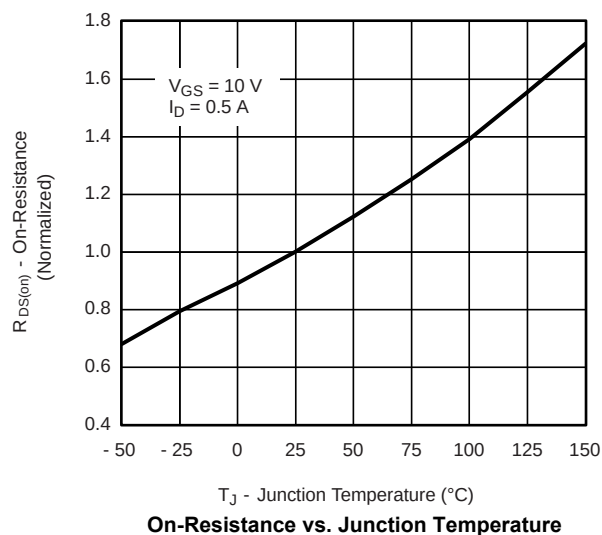
SPECIFICATIONS T _J = 25 °C, unless otherwise noted								
Parameter	Symbol	Test Conditions		Min.	Typ.	Max.	Unit	
Static								
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	N-Ch	1.0	2.0	3.0	V	
		V _{DS} = V _{GS} , I _D = - 250 μA	P-Ch	- 1.0	1.5	-2.5		
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	N-Ch P-Ch			± 100 ± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V	N-Ch			1	μA	
		V _{DS} = - 60 V, V _{GS} = 0 V	P-Ch			- 1		
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 55 °C	N-Ch			5		
		V _{DS} = - 60 V, V _{GS} = 0 V, T _J = 55 °C	P-Ch			- 5		
On-State Drain Current ^a	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	N-Ch	3.7			A	
		V _{DS} = - 5 V, V _{GS} = - 10 V	P-Ch	- 3				
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 0.5 A	N-Ch		0.700		Ω	
		V _{GS} = - 10 V, I _D = - 0.3 A	P-Ch		2.060			
		V _{GS} = 4.5 V, I _D = 0.4A	N-Ch		0.850			
		V _{GS} = - 4.5 V, I _D = - 0.2 A	P-Ch		2.410			
Forward Transconductance ^a	g _{fs}	V _{DS} = 10 V, I _D = 0.5 A	N-Ch		4.3		S	
		V _{DS} = - 15 V, I _D = - 0.3 A	P-Ch		2.4			
Diode Forward Voltage ^a	V _{SD}	I _S = 0.45 A, V _{GS} = 0 V	N-Ch		0.81	1.10	V	
		I _S = - 0.35 A, V _{GS} = 0 V	P-Ch		- 0.83	- 1.10		
Dynamic ^b								
Total Gate Charge	Q _g	N-Channel V _{DS} = 30V, V _{GS} = 5 V, I _D = 0.5 A	N-Ch P-Ch		0.7 0.8	1.1 1.2	nC	
Gate-Source Charge	Q _{gs}		N-Ch P-Ch		0.3 0.4			
Gate-Drain Charge	Q _{gd}	P-Channel V _{DS} = - 30V, V _{GS} = - 5 V, I _D = - 0.3 A	N-Ch P-Ch		0.2 0.3			
Gate Resistance	R _g		N-Ch P-Ch	0.5 3		2.4 11	Ω	
Turn-On Delay Time	t _{d(on)}	N-Channel V _{DD} = 15 V, R _L = 15 Ω I _D ≅0.5 A, V _{GEN} = 10 V, R _g = 6 Ω	N-Ch P-Ch		7 8	11 12	ns	
Rise Time	t _r		N-Ch P-Ch		9 12	14 18		
Turn-Off Delay Time	t _{d(off)}		P-Channel V _{DD} = - 15 V, R _L = 15 Ω I _D ≅ - 0.3 A,V _{GEN} = - 10 V, R _g = 6 Ω	N-Ch P-Ch		13 12		20 18
				N-Ch P-Ch		5 7		8 11
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 0.45 A, dI/dt = 100 A/μs	N-Ch		25	40		
		I _F = - 0.35 A, dI/dt = 100 A/μs	P-Ch		20	40		

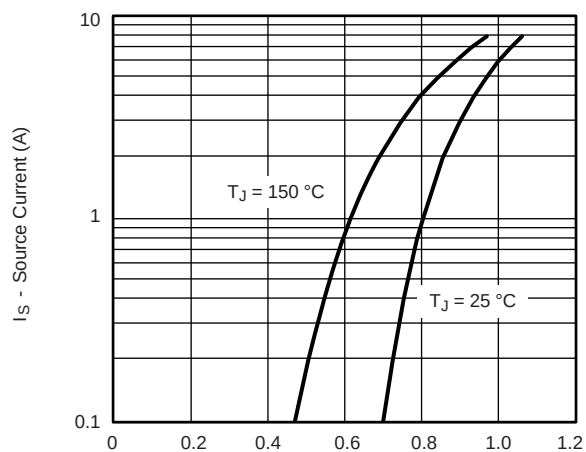
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

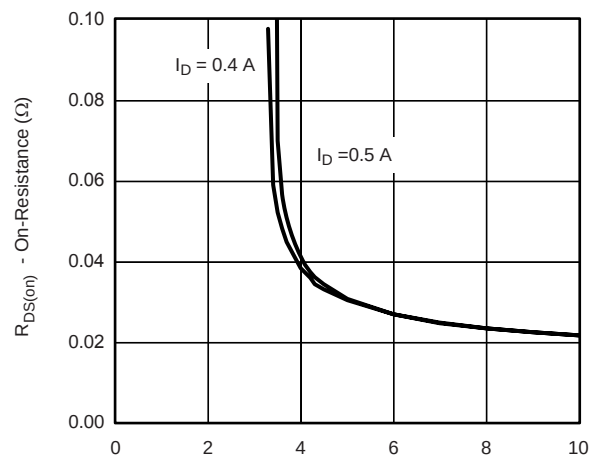
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

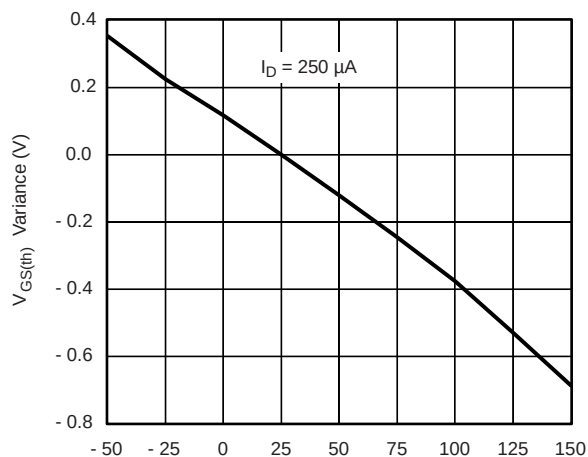
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


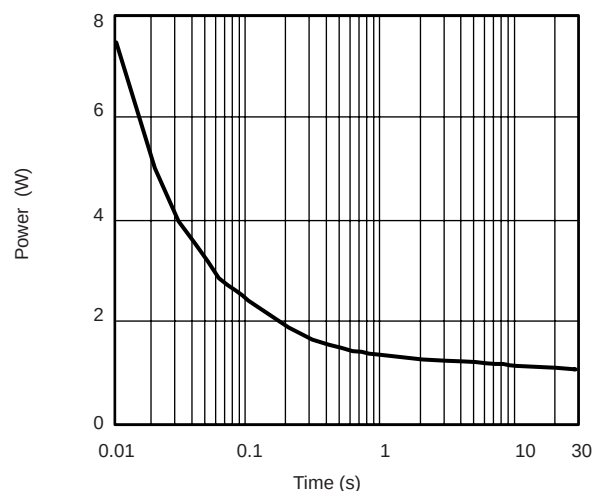
V_{SD} - Source-to-Drain Voltage (V)
Source-Drain Diode Forward Voltage



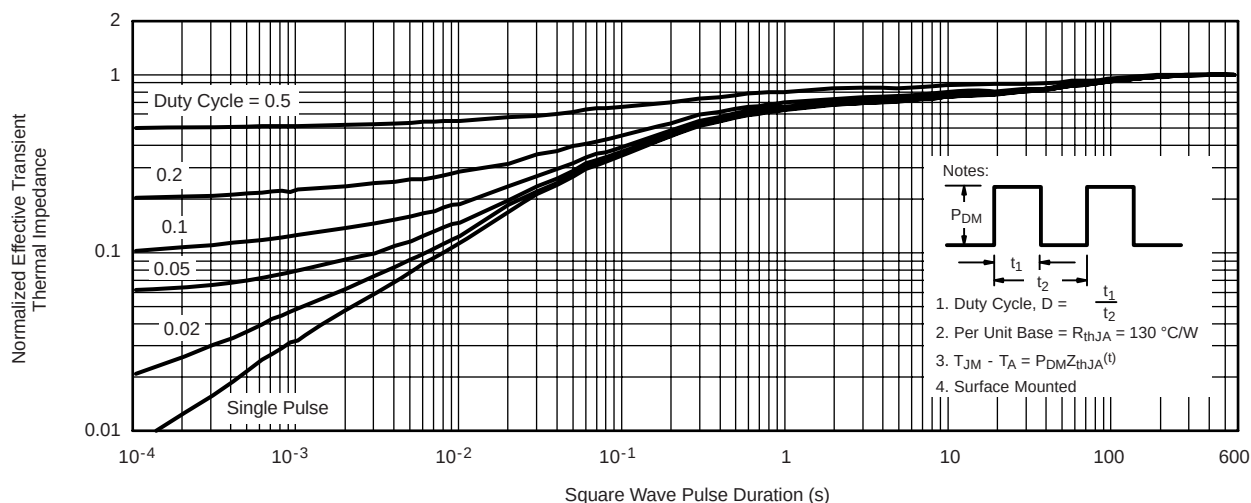
On-Resistance vs. Gate-to-Source Voltage



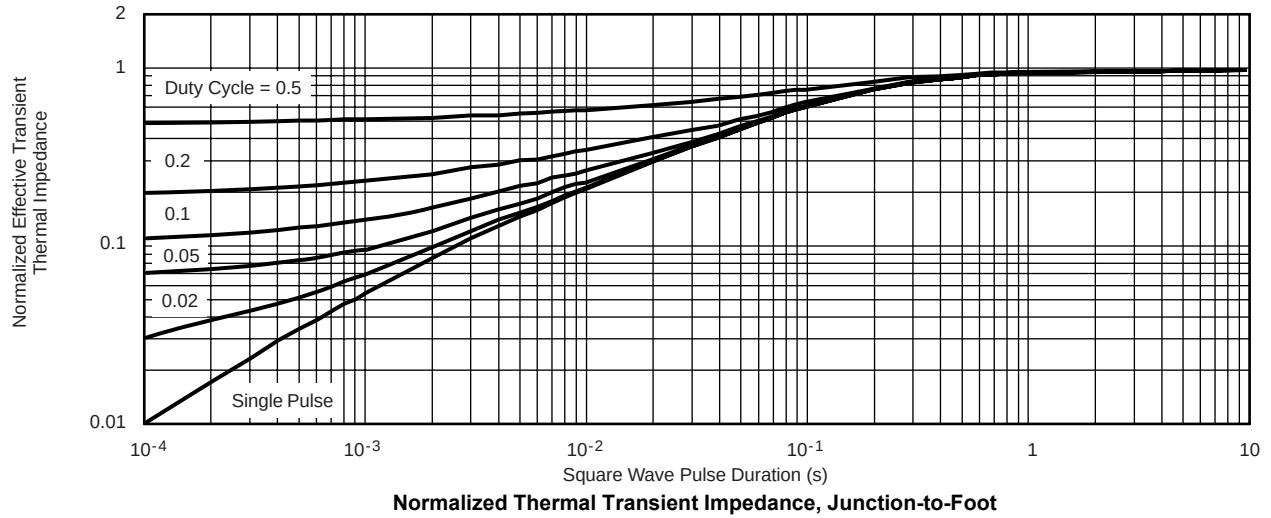
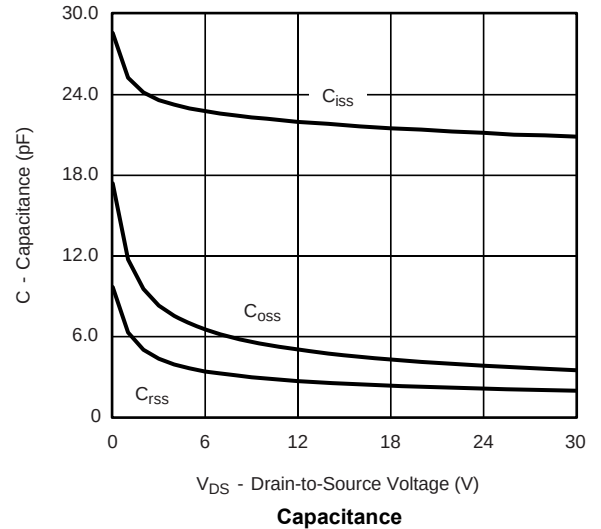
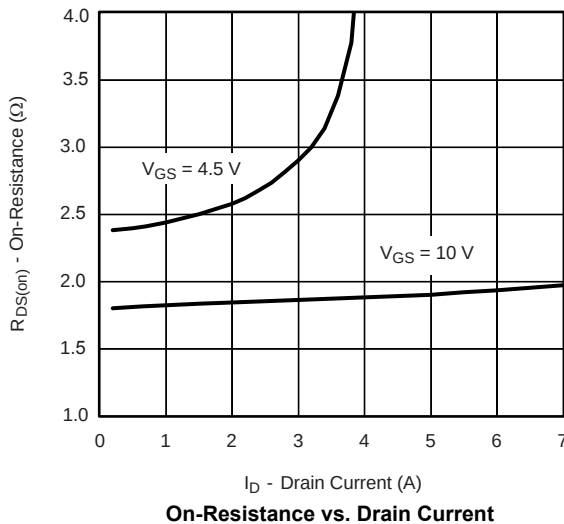
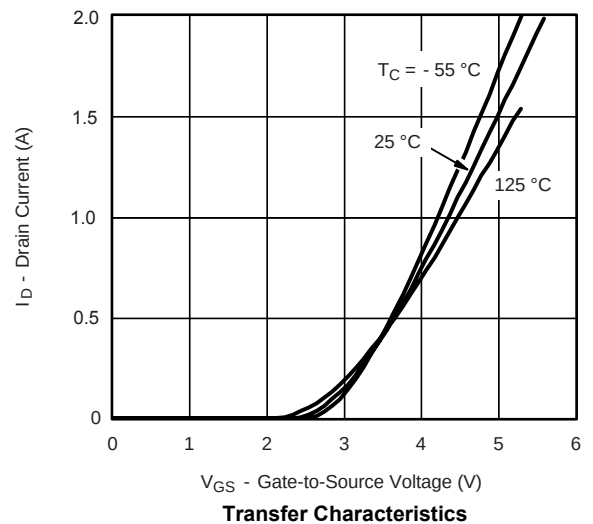
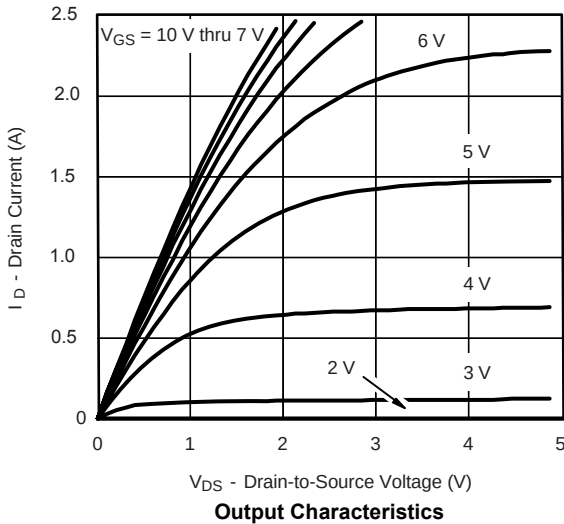
Threshold Voltage

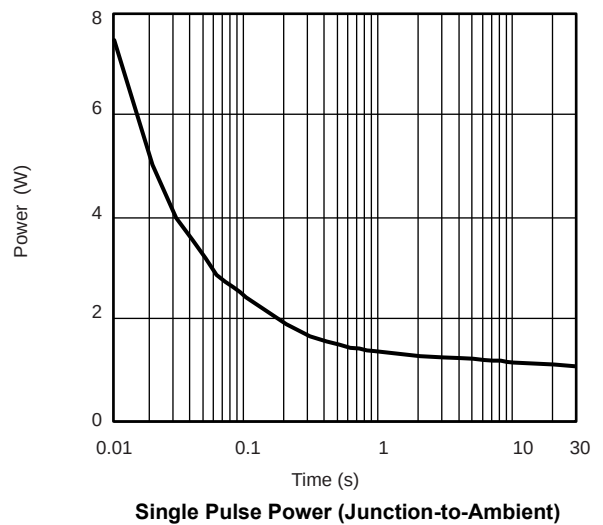
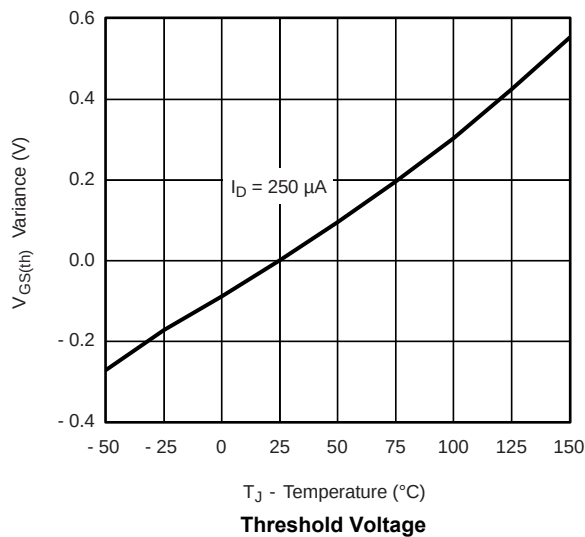
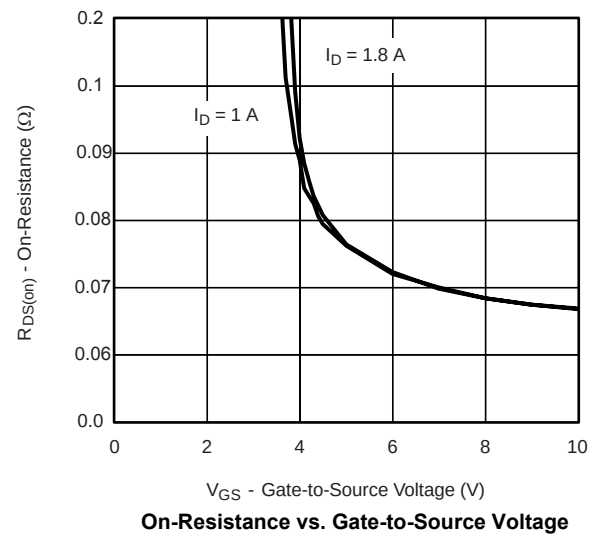
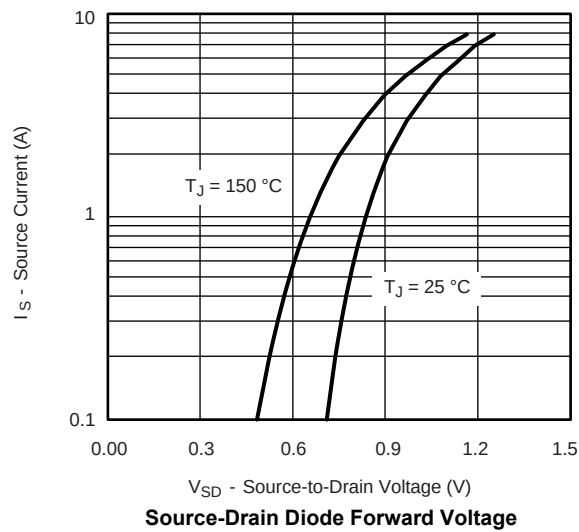
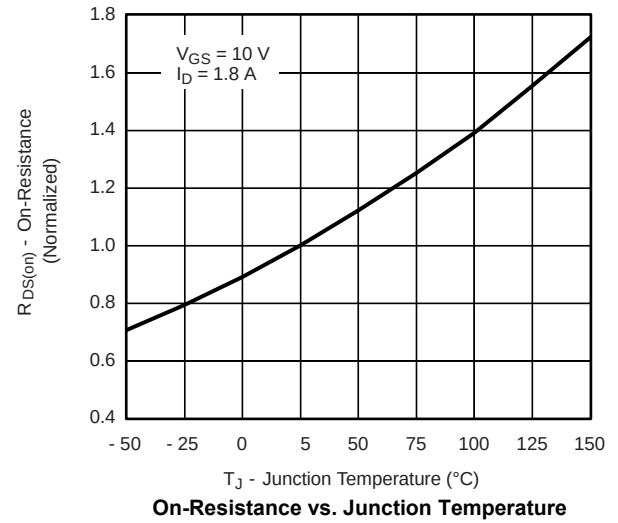
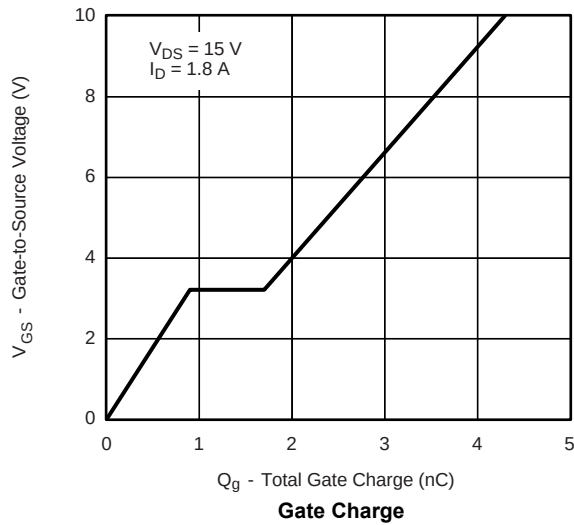


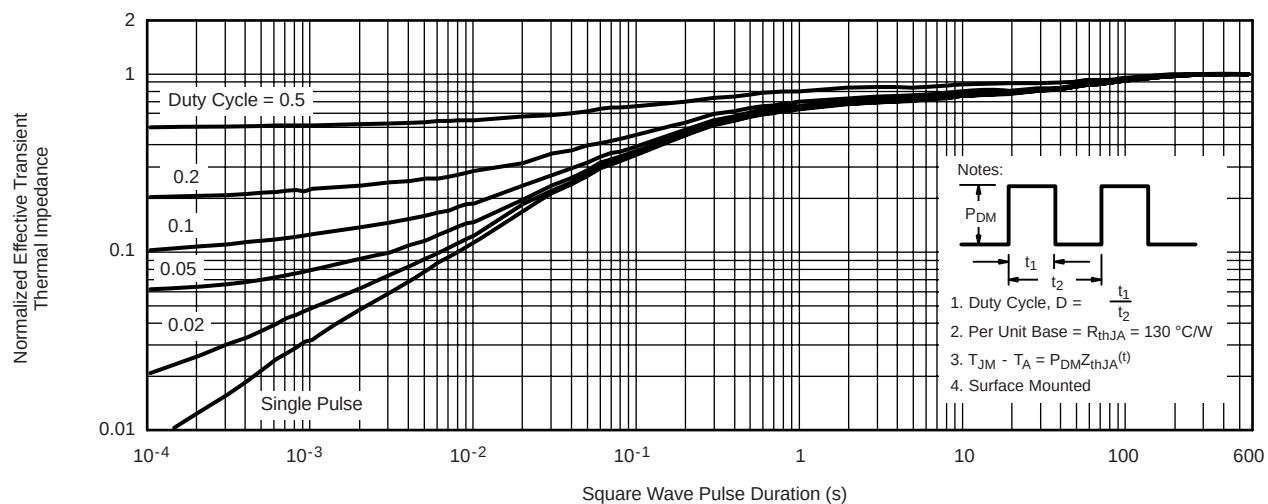
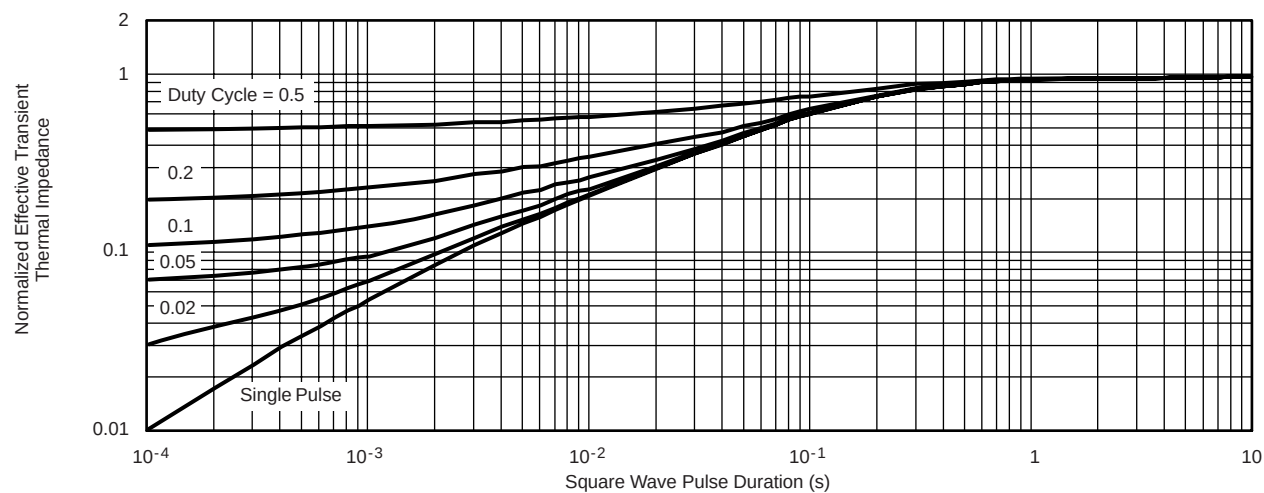
Single Pulse Power (Junction-to-Ambient)



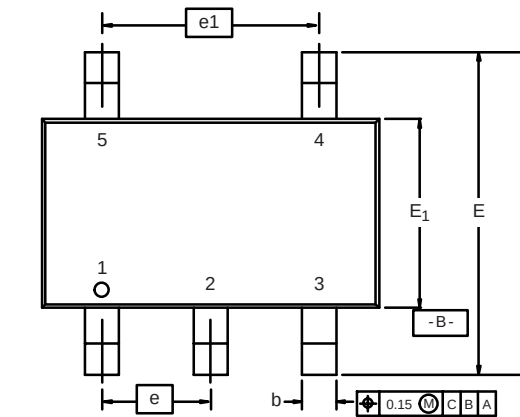
Normalized Thermal Transient Impedance, Junction-to-Ambient

N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


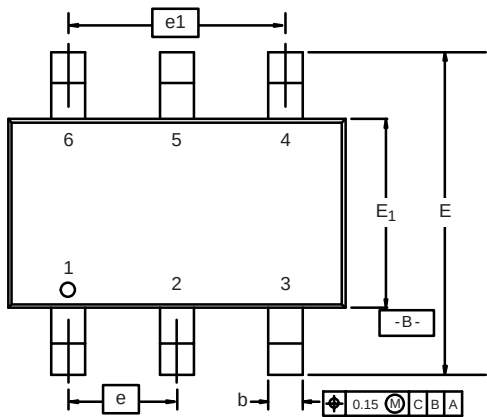
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Normalized Thermal Transient Impedance, Junction-to-Ambient

Normalized Thermal Transient Impedance, Junction-to-Foot

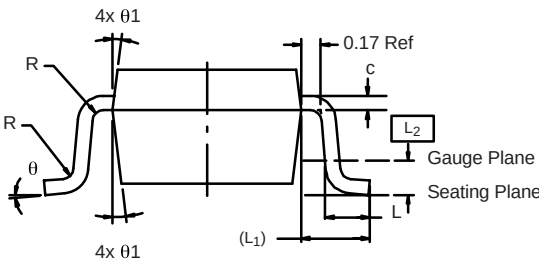
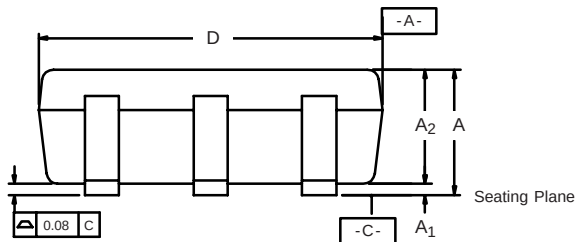
TSOP: 5/6-LEAD
JEDEC Part Number: MO-193C



5-LEAD TSOP

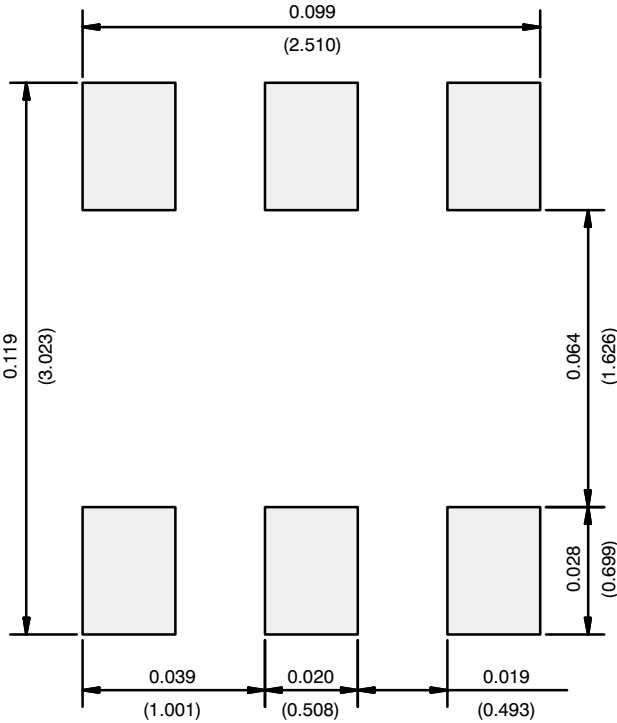


6-LEAD TSOP



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.91	-	1.10	0.036	-	0.043
A ₁	0.01	-	0.10	0.0004	-	0.004
A ₂	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E ₁	1.55	1.65	1.70	0.061	0.065	0.067
e	0.95 BSC			0.0374 BSC		
e ₁	1.80	1.90	2.00	0.071	0.075	0.079
L	0.32	-	0.50	0.012	-	0.020
L ₁	0.60 Ref			0.024 Ref		
L ₂	0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ ₁	7° Nom			7° Nom		
ECN: C-06593-Rev. I, 18-Dec-06						
DWG: 5540						

RECOMMENDED MINIMUM PADS FOR TSOP-6



Recommended Minimum Pads
Dimensions in Inches/(mm)

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